

P-Channel Enhancement Mode Power MOSFET

Description

The RM50P30D3 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

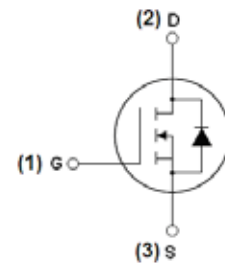
General Features

- $V_{DS} = -30V, I_D = -50A$
 $R_{DS(ON)} < 8.7m\Omega @ V_{GS} = -10V$
 $R_{DS(ON)} < 13.5m\Omega @ V_{GS} = -4.5V$
- High density cell design for ultra low $R_{ds(on)}$
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

- Load switching
- Hard switched and high frequency circuits
- Uninterruptible power supply
- Halogen-free
- P/N suffix V means AEC-Q101 qualified, e.g:RM50P30D3

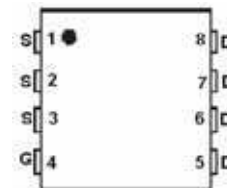
100% UIS TESTED!
100% ΔV_{ds} TESTED!



Schematic diagram



pin assignment



DFN 3x3 EP top view

Package Marking and Ordering Information

| Device Marking | Device | Device Package | Reel Size | Tape width | Quantity |
|----------------|-----------|----------------|-----------|------------|----------|
| 50P30 | RM50P30D3 | DFN 3X3 | - | - | - |

Absolute Maximum Ratings ($T_C=25^\circ C$ unless otherwise noted)

| Parameter | Symbol | Limit | Unit |
|---|--------------------|------------|------------|
| Drain-Source Voltage | V_{DS} | -30 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | V |
| Drain Current-Continuous | I_D | -50 | A |
| Drain Current-Continuous($T_C=100^\circ C$) | $I_D(100^\circ C)$ | -32 | A |
| Pulsed Drain Current | I_{DM} | -200 | A |
| Maximum Power Dissipation | P_D | 38 | W |
| Single pulse avalanche energy ^(Note 5) | E_{AS} | 125 | mJ |
| Operating Junction and Storage Temperature Range | T_J, T_{STG} | -55 To 150 | $^\circ C$ |

Thermal Characteristic

| | | | |
|--|-----------------|-----|------|
| Thermal Resistance, Junction-to-Case ^(Note 2) | $R_{\theta JC}$ | 2.3 | °C/W |
|--|-----------------|-----|------|

Electrical Characteristics ($T_C=25^\circ\text{C}$ unless otherwise noted)

| Parameter | Symbol | Condition | Min | Typ | Max | Unit |
|--|--------------|--|------|------|-----------|------------|
| Off Characteristics | | | | | | |
| Drain-Source Breakdown Voltage | BV_{DSS} | $V_{GS}=0V, I_D=-250\mu A$ | -30 | - | - | V |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS}=-24V, V_{GS}=0V$ | - | - | 1 | μA |
| Gate-Body Leakage Current | I_{GSS} | $V_{GS}=\pm 20V, V_{DS}=0V$ | - | - | ± 100 | nA |
| On Characteristics ^(Note 3) | | | | | | |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS}=V_{GS}, I_D=-250\mu A$ | -1.2 | - | -2.5 | V |
| Drain-Source On-State Resistance | $R_{DS(on)}$ | $V_{GS}=-10V, I_D=-30A$ | - | 7.3 | 8.7 | m Ω |
| | | $V_{GS}=-4.5V, I_D=-15A$ | - | 11 | 13.5 | m Ω |
| Forward Transconductance | g_{FS} | $V_{DS}=-5V, I_D=-18A$ | - | 25 | - | S |
| Dynamic Characteristics ^(Note 4) | | | | | | |
| Input Capacitance | C_{iss} | $V_{DS}=-15V, V_{GS}=0V,$ $F=1.0\text{MHz}$ | - | 3448 | - | PF |
| Output Capacitance | C_{oss} | | - | 508 | - | PF |
| Reverse Transfer Capacitance | C_{rss} | | - | 421 | - | PF |
| Switching Characteristics ^(Note 4) | | | | | | |
| Turn-on Delay Time | $t_{d(on)}$ | $V_{DD}=-15V, I_D=-15A, R_L=1\Omega$ $V_{GS}=-10V, R_G=3.3\Omega$ | - | 9.4 | - | nS |
| Turn-on Rise Time | t_r | | - | 10.2 | - | nS |
| Turn-Off Delay Time | $t_{d(off)}$ | | - | 117 | - | nS |
| Turn-Off Fall Time | t_f | | - | 24 | - | nS |
| Total Gate Charge | Q_g | $V_{DS}=-15V, I_D=-15A,$ $V_{GS}=-4.5V$ | - | 30 | - | nC |
| Gate-Source Charge | Q_{gs} | | - | 10 | - | nC |
| Gate-Drain Charge | Q_{gd} | | - | 10.4 | - | nC |
| Drain-Source Diode Characteristics | | | | | | |
| Diode Forward Voltage ^(Note 3) | V_{SD} | $V_{GS}=0V, I_S=-1A$ | - | - | -1 | V |
| Diode Forward Current ^(Note 2) | I_S | | - | - | -50 | A |

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, $t \leq 10$ sec.

3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.

4. Guaranteed by design, not subject to production

5. E_{AS} condition : $T_j=25^\circ\text{C}, V_{DD}=20V, V_G=10V, L=1\text{mH}, R_G=25\Omega,$



RATING AND CHARACTERISTICS CURVES (RM50P30D3)

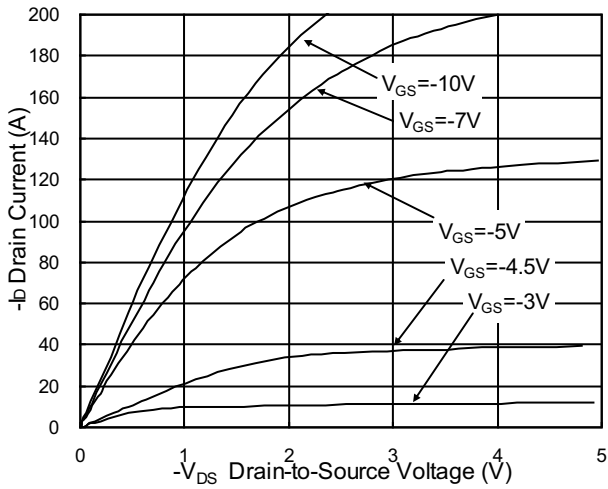


Fig.1 Typical Output Characteristics

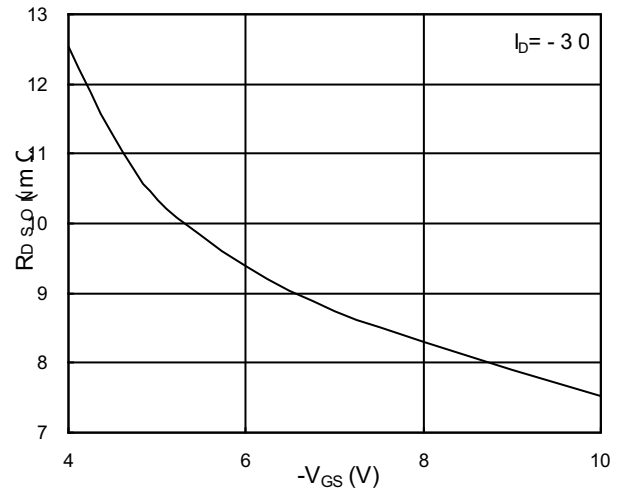


Fig.2 On-Resistance v.s Gate-Source

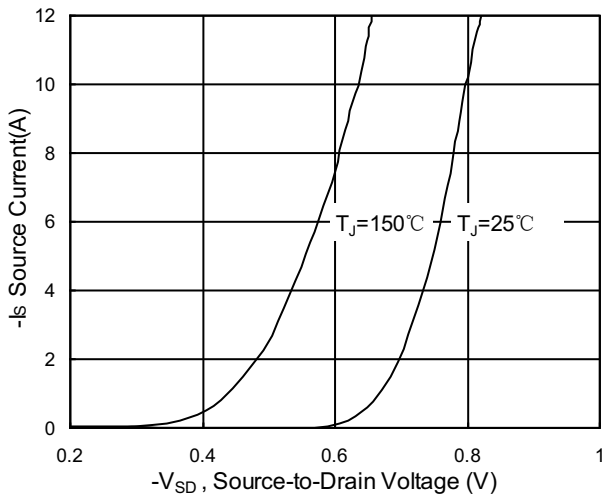


Fig.3 Forward Characteristics Of Reverse

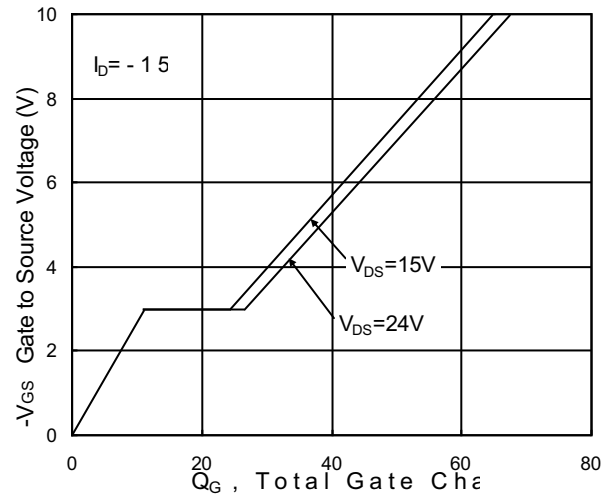


Fig.4 Gate-Charge Characteristics

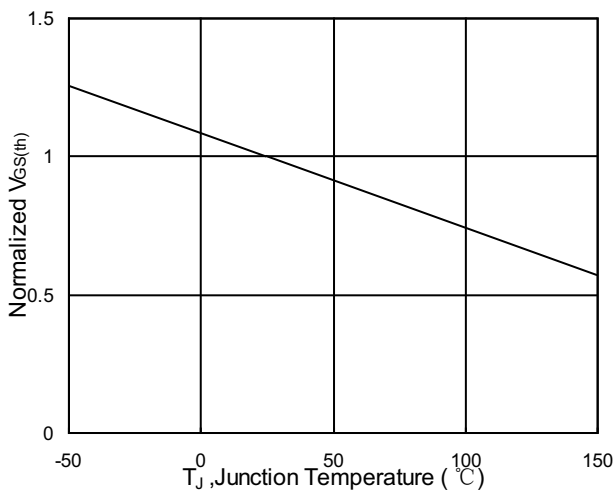


Fig.5 Normalized $V_{GS(th)}$ v.s T_J

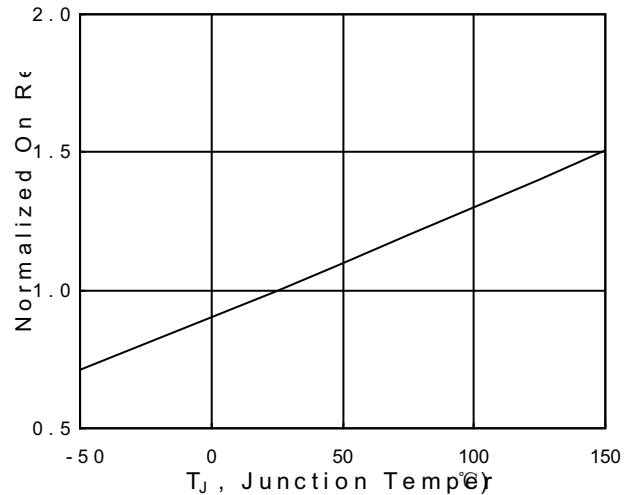


Fig.6 Normalized $R_{DS(on)}$ v.s T_J

RATING AND CHARACTERISTICS CURVES (RM50P30D3)

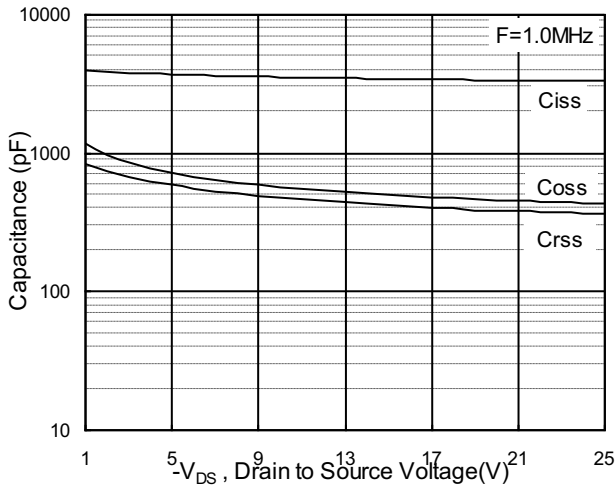


Fig.7 Capacitance

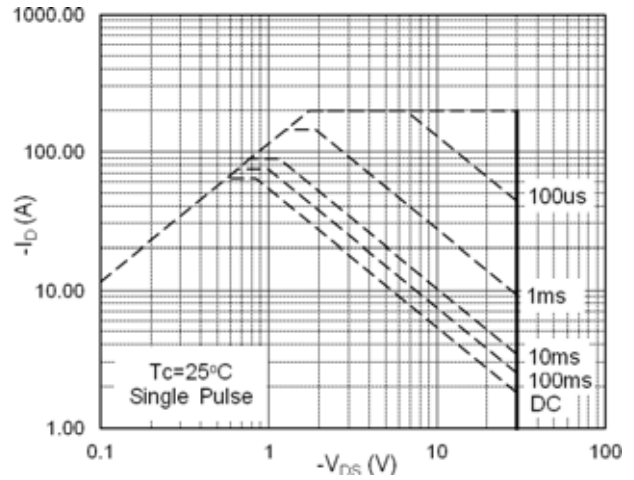


Fig.8 Safe Operating Area

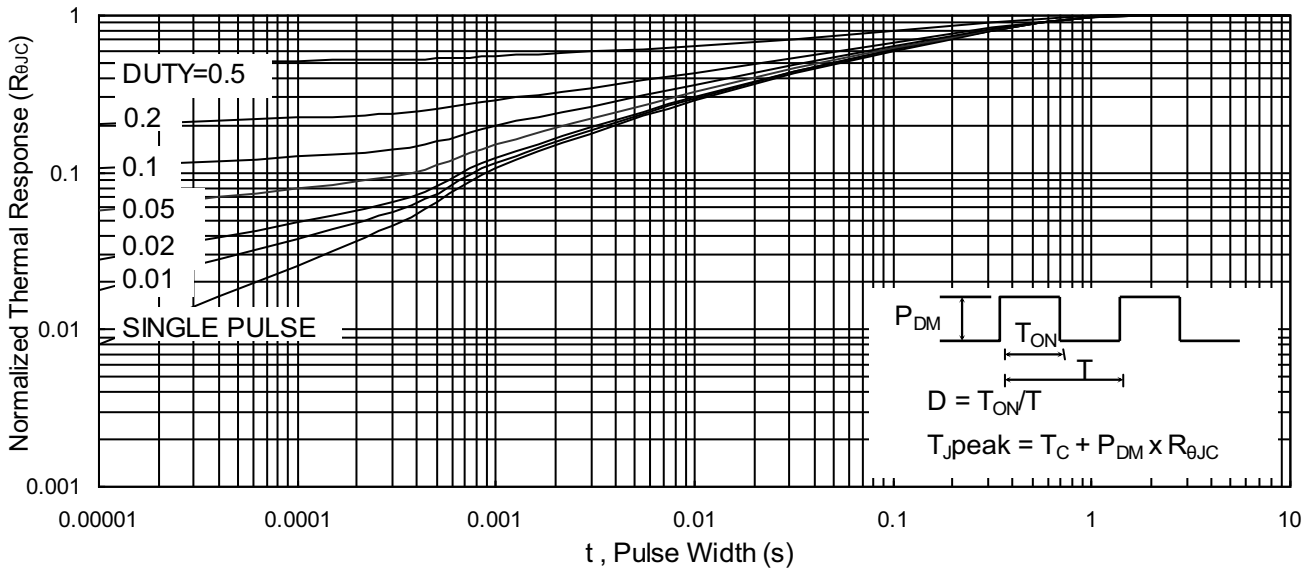


Fig.9 Normalized Maximum Transient Thermal Impedance

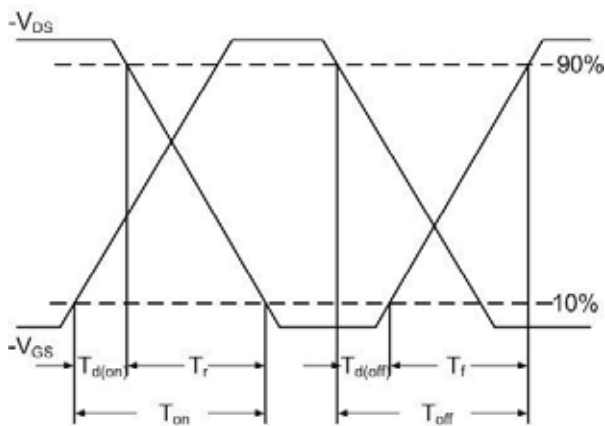


Fig.10 Switching Time Waveform

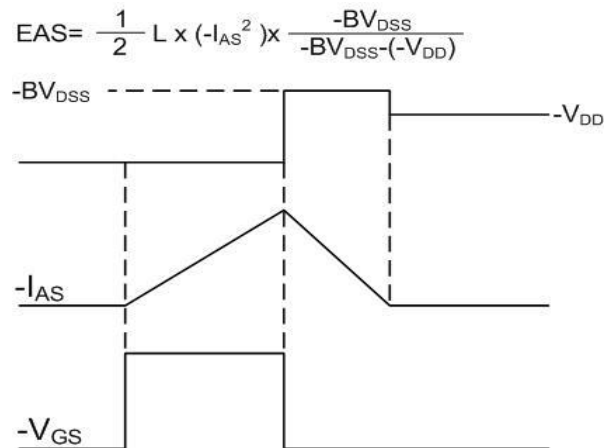
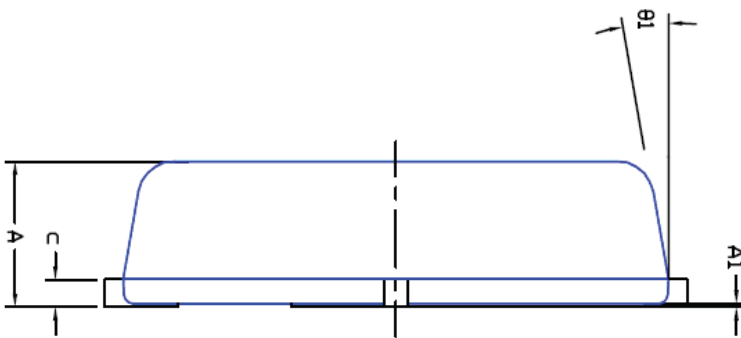
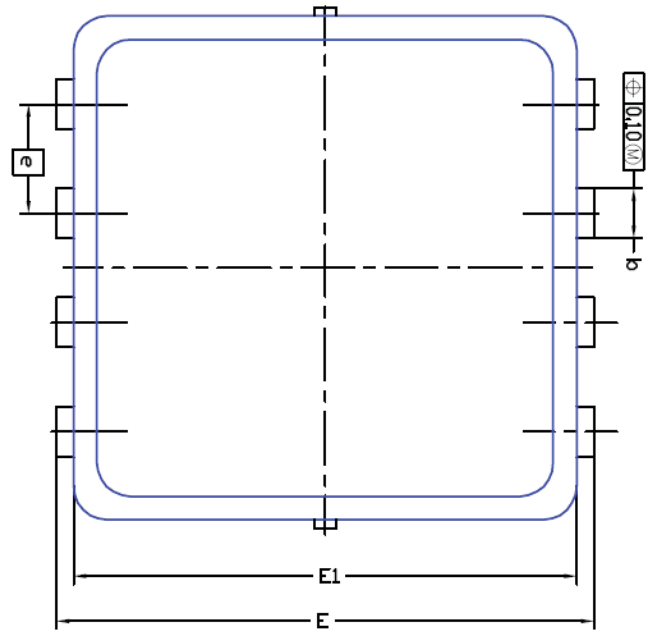
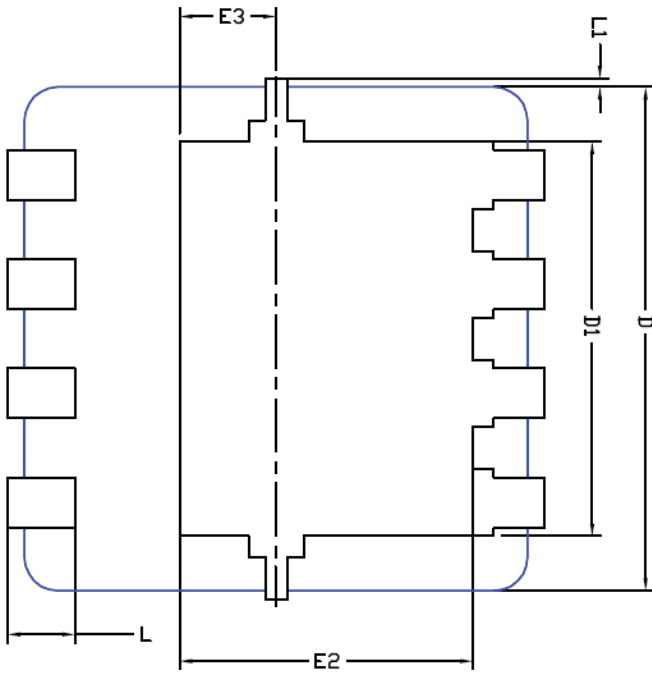


Fig.11 Unclamped Inductive Switching Waveform

DFN3X3 EP Package Information



| DIM. | MILLIMETERS | | | INCHES | | |
|------|-------------|-------|-------|-----------|--------|--------|
| | MIN | NOM | MAX | MIN | NOM | MAX |
| A | 0.700 | 0.80 | 0.900 | 0.0276 | 0.0315 | 0.0354 |
| A1 | 0.00 | --- | 0.05 | 0.000 | --- | 0.002 |
| b | 0.24 | 0.30 | 0.35 | 0.009 | 0.012 | 0.014 |
| c | 0.10 | 0.152 | 0.25 | 0.004 | 0.006 | 0.010 |
| D | 3.00 BSC | | | 0.118 BSC | | |
| D1 | 2.35 BSC | | | 0.093 BSC | | |
| E | 3.20 BSC | | | 0.126 BSC | | |
| E1 | 3.00 BSC | | | 0.118 BSC | | |
| E2 | 1.75 BSC | | | 0.069 BSC | | |
| E3 | 0.575 BSC | | | 0.023 BSC | | |
| e | 0.65 BSC | | | 0.026 BSC | | |
| L | 0.30 | 0.40 | 0.50 | 0.0118 | 0.0157 | 0.0197 |
| L1 | 0 | --- | 0.100 | 0 | --- | 0.004 |
| θ1 | 0° | 10° | 12° | 0° | 10° | 12° |

| Package | Tube (pcs/tube) | Tube (pcs/inner box) | Tube (pcs/cartoon) | Tape&Reel (pcs/reel) | Tape&Reel (pcs/inner box) | Tape&Reel (pcs/cartoon) |
|---------------|--------------------|-------------------------|-----------------------|-------------------------|------------------------------|----------------------------|
| DFN5x6/DFN3x3 | 100 | 10,000 | 100,000 | 2,500 | 5,000 | 40,000 |
| DFN1006 | — | — | — | 10,000 | 10,000 | 400,000 |
| SOP-8 | 100 | 10,000 | 100,000 | 4,000 | 4,000 | 64,000 |
| TSSOP-8 | 100 | 32,000 | 128,000 | 3,000 | 6,000 | 48,000 |
| SOT-23-3L | — | — | — | 3,000 | 30,000 | 120,000 |
| SOT-23-6L | — | — | — | 3,000 | 30,000 | 120,000 |
| SOT-23(6R) | — | — | — | 3,000 | 30,000 | 120,000 |
| SOT-363 | — | — | — | 3,000 | 30,000 | 120,000 |
| SOT-523 | — | — | — | 3,000 | 30,000 | 120,000 |
| SOT223 | — | — | — | 2,500 | 2,500 | 20,000 |
| TO-220 | 50 | 1,000 | 5,000 | — | — | — |
| TO-220F | 50 | 1,000 | 10,000 | — | — | — |
| TO-247 | 30 | 300 | 1,200 | — | — | — |
| TO-251 | 80 | 4,000 | 40,000 | — | — | — |
| TO-251S(4R) | 80 | 4,000 | 40,000 | — | — | — |
| TO-252-2L(4R) | 80 | 4,000 | 40,000 | 2,500 | 2,500 | 25,000 |
| TO-263-2L | 50 | 1,000 | 10,000 | 800 | 800 | 8,000 |
| TO-3P | 30 | 300 | 3,000 | — | — | — |
| TO-92 | — | — | — | 1,000(袋装) | 10,000 | 100,000 |

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